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(Please amend Claim 39 as follows:)

39. (Amended) A varistor, comprising:

a semiconductor body including conductive plates interleaved between zinc oxide layers, the body surface being untreated and including an interior region and a plurality of separate terminal regions;

silver barriers formed directly on the terminal regions; and

nickel barrier caps formed on the silver barriers by bringing only the silver barriers into contact with a nickel plating solution such that the nickel plating solution bonds to the silver barriers but not the semiconductive interior region.

(Please amend Claim 40 as follows:)

40. (Amended) The varistor according to Claim 39, further including tin barriers formed on the nickel barrier caps.

Please add new Claim 42 as follows:

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42. (Newly Added) The varistor of Claim 36, wherein the terminal regions are located at opposing ends of the body.

(Please add new Claim 43 as follows:)

43. (Newly Added) The varistor of Claim 36, further comprising tin barriers formed on the nickel barrier caps.

(Please add new Claim 44 as follows:)

44. (Newly Added) The varistor of Claim 36, wherein the zinc oxide layers further include a ceramic material.

(Please add new Claim 45 as follows:)

45. (Newly Added) The varistor of Claim 39, wherein the terminal regions are located at opposing ends of the body.

⌈ Please add new Claim 46 as follows: ⌋

46. (Newly Added) The varistor of Claim 39, wherein the zinc oxide layers further include a ceramic material.

⌈ Please add new Claim 47 as follows: ⌋

47. (Newly Added) The varistor of Claim 39, wherein the terminal regions are located at opposing ends of the body.

⌈ Please add new Claim 48 as follows: ⌋

48. (Newly Added) A varistor, comprising:
a semiconductor body including electrically conductive plates interleaved between zinc oxide layers, an interior region and a plurality of separate terminal regions; and
nickel barrier caps formed by directly contacting the semiconductor terminal regions of the semiconductor body with a nickel plating solution in order to form a desirably thick nickel barrier cap over the terminal regions of the semiconductor body without forming a nickel barrier over the interior region of the semiconductor body.

⌈ Please add new Claim 49 as follows: ⌋

49. (Newly Added) The varistor of Claim 48, further comprising tin barriers formed on the nickel barrier caps.

⌈ Please add new Claim 50 as follows: ⌋

50. (Newly Added) The varistor of Claim 48, wherein each nickel barrier cap is between about 1 and about 3 μm thick.

⌈ Please add new Claim 51 as follows: ⌋

51. (Newly Added) The varistor of Claim 48, wherein the terminal regions are located at opposing ends of the semiconductor body.
